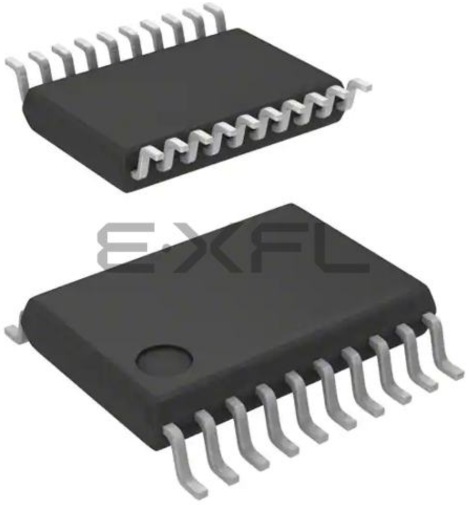


What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	15
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21324mdsp-u0

Table 1.2 Specifications for R8C/32M Group (2)

Item	Function	Specification
Serial Interface	UART0	Clock synchronous serial I/O/UART
	UART2	Clock synchronous serial I/O/UART, I^2C mode (I^2C-bus), multiprocessor communication function
Synchronous Serial Communication Unit (SSU)		1 (shared with I^2C-bus)
I^2C bus		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 4 channels, includes sample and hold function, with sweep mode
Comparator A		• 2 circuits (shared with voltage monitor 1 and voltage monitor 2) • External reference voltage input available
Comparator B		2 circuits
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 10,000 times (data flash) 1,000 times (program ROM) • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function • Background operation (BGO) function
Operating Frequency/Supply Voltage		f(XIN) = 20 MHz (VCC = 2.7 to 5.5 V) f(XIN) = 5 MHz (VCC = 1.8 to 5.5 V)
Current consumption		Typ. 6.5 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 3.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 3.5 µA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz)) Typ. 2.0 µA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature		-20 to 85°C (N version) -40 to 85°C (D version) (1)
Package		20-pin LSSOP Package code: PLSP0020JB-A (previous code: 20P2F-A)

Note:

1. Specify the D version if D version functions are to be used.

Table 1.4 Pin Name Information by Pin Number

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, Comparator A, Comparator B
1		P4_2						VREF
2	MODE							
3	$\overline{\text{RESET}}$							
4	XOUT(/XCOUT)	P4_7						
5	VSS/AVSS							
6	XIN(/XCIN)	P4_6						
7	VCC/AVCC							
8		P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA	
9		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
10		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3
11		P3_3	$\overline{\text{INT3}}$	(TRCCLK)	($\overline{\text{CTS2}}$/$\overline{\text{RTS2}}$)	$\overline{\text{SCS}}$		IVCMP3
12		P4_5	$\overline{\text{INT0}}$		(RXD2/SCL2)			$\overline{\text{ADTRG}}$
13		P1_7	$\overline{\text{INT1}}$	(TRAIO)				IVCMP1
14		P1_6			(CLK0)			LVCOUT2/IVREF1
15		P1_5	($\overline{\text{INT1}}$)	(TRAIO)	(RXD0)			
16		P1_4		(TRCCLK)	(TXD0)			
17		P1_3	$\overline{\text{KI3}}$	TRBO (/TRCIOC)				AN11/LVCOUT1
18		P1_2	$\overline{\text{KI2}}$	(TRCIOB)				AN10/LVREF
19		P1_1	$\overline{\text{KI1}}$	(TRCIOA/ TRCTRG)				AN9/LVCMP2
20		P1_0	$\overline{\text{KI0}}$	(TRCIOD)				AN8/LVCMP1

Note:

1. Can be assigned to the pin in parentheses by a program.

Table 1.6 Pin Functions (2)

Item	Pin Name	I/O Type	Description
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter
A/D converter	AN8 to AN11	I	Analog input pins to A/D converter
	$\overline{\text{ADTRG}}$	I	A/D external trigger input pin
Comparator A	LVCMP1, LVCMP2	I	Comparator A analog voltage input pins
	LVREF	I	Comparator A reference voltage input pin
	LVCOUT1, LVCOUT2	O	Comparator A output pins
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins
	IVREF1, IVREF3	I	Comparator B reference voltage input pins
I/O port	P1_0 to P1_7, P3_3 to P3_5, P3_7, P4_5 to P4_7	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. All ports can be used as LED drive ports.
Input port	P4_2	I	Input-only port

I: Input O: Output I/O: Input and output

3. Memory

3.1 R8C/32M Group

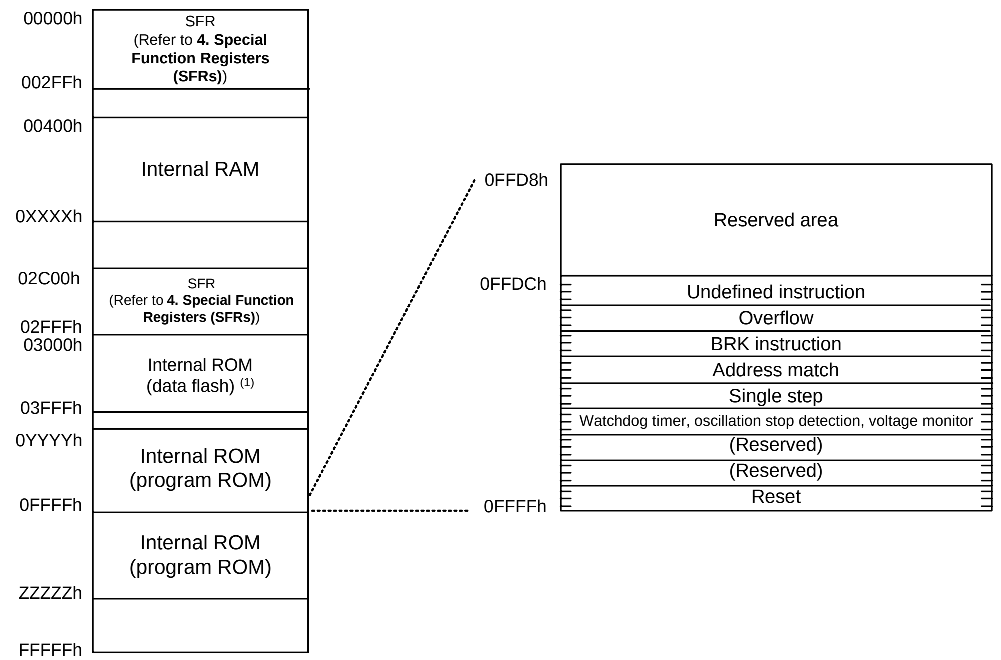
Figure 3.1 is a Memory Map of R8C/32M Group. The R8C/32M Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.

The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1.5-Kbyte internal RAM area is allocated addresses 00400h to 009FFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. Data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F21321MNFP, R5F21321MDFP	4 Kbytes	0F000h	–	512 bytes	005FFh
R5F21322MNFP, R5F21322MDFP	8 Kbytes	0E000h	–	1 Kbyte	007FFh
R5F21324MNFP, R5F21324MDFP	16 Kbytes	0C000h	–	1.5 Kbytes	009FFh

Figure 3.1 Memory Map of R8C/32M Group

Table 4.2 SFR Information (2) (1)

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h			
0044h			
0045h			
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h			
0049h			
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register / IIC bus Interrupt Control Register (2)	SSUIC / IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h			
0054h			
0055h			
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh			
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	UART2 Bus Collision Detection Interrupt Control Register	U2BCNIC	XXXXX000b
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage Monitor 1 / Comparator A1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage Monitor 2 / Comparator A2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.3 SFR Information (3) (1)

Address	Register	Symbol	After Reset
0080h	DTC Activation Control Register	DTCTL	00h
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h	DTC Activation Enable Register 0	DTCEN0	00h
0089h	DTC Activation Enable Register 1	DTCEN1	00h
008Ah	DTC Activation Enable Register 2	DTCEN2	00h
008Bh	DTC Activation Enable Register 3	DTCEN3	00h
008Ch			
008Dh	DTC Activation Enable Register 5	DTCEN5	00h
008Eh	DTC Activation Enable Register 6	DTCEN6	00h
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit / Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit / Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit / Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART2 Transmit / Receive Mode Register	U2MR	00h
00A9h	UART2 Bit Rate Register	U2BRG	XXh
00AAh	UART2 Transmit Buffer Register	U2TB	XXh
00ABh			XXh
00ACh	UART2 Transmit / Receive Control Register 0	U2C0	00001000b
00ADh	UART2 Transmit / Receive Control Register 1	U2C1	00000010b
00AEh	UART2 Receive Buffer Register	U2RB	XXh
00AFh			XXh
00B0h	UART2 Digital Filter Function Select Register	URXDF	00h
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh	UART2 Special Mode Register 5	U2SMR5	00h
00BCh	UART2 Special Mode Register 4	U2SMR4	00h
00BDh	UART2 Special Mode Register 3	U2SMR3	000X0X0Xb
00BEh	UART2 Special Mode Register 2	U2SMR2	X0000000b
00BFh	UART2 Special Mode Register	U2SMR	X0000000b

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.4 SFR Information (4) (1)

Address	Register	Symbol	After Reset
00C0h	A/D Register 0	AD0	XXh
00C1h			000000XXb
00C2h	A/D Register 1	AD1	XXh
00C3h			000000XXb
00C4h	A/D Register 2	AD2	XXh
00C5h			000000XXb
00C6h	A/D Register 3	AD3	XXh
00C7h			000000XXb
00C8h	A/D Register 4	AD4	XXh
00C9h			000000XXb
00CAh	A/D Register 5	AD5	XXh
00CBh			000000XXb
00CCh	A/D Register 6	AD6	XXh
00CDh			000000XXb
00CEh	A/D Register 7	AD7	XXh
00CFh			000000XXb
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Mode Register	ADMOD	00h
00D5h	A/D Input Select Register	ADINSEL	11000000b
00D6h	A/D Control Register 0	ADCON0	00h
00D7h	A/D Control Register 1	ADCON1	00h
00D8h			
00D9h			
00DAh			
00DBh			
00DCh			
00DDh			
00DEh			
00DFh			
00E0h			
00E1h	Port P1 Register	P1	XXh
00E2h			
00E3h	Port P1 Direction Register	PD1	00h
00E4h			
00E5h	Port P3 Register	P3	XXh
00E6h			
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h			
00EAh	Port P4 Direction Register	PD4	00h
00EBh			
00ECh			
00EDh			
00EEh			
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.12 SFR Information (12) (1)

Address	Register	Symbol	After Reset
2CF0h	DTC Control Data 22	DTCD22	XXh
2CF1h			XXh
2CF2h			XXh
2CF3h			XXh
2CF4h			XXh
2CF5h			XXh
2CF6h			XXh
2CF7h			XXh
2CF8h	DTC Control Data 23	DTCD23	XXh
2CF9h			XXh
2CFAh			XXh
2CFBh			XXh
2CFCh			XXh
2CFDh			XXh
2CFEh			XXh
2CFFh			XXh
2D00h			
:			
2FFFh			

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

Table 4.13 ID Code Areas and Option Function Select Area

Address	Area Name	Symbol	After Reset
:			
FFDBh	Option Function Select Register 2	OFS2	(Note 1)
:			
FFDFh	ID1		(Note 2)
:			
FFE3h	ID2		(Note 2)
:			
FFEBh	ID3		(Note 2)
:			
FFEFh	ID4		(Note 2)
:			
FFF3h	ID5		(Note 2)
:			
FFF7h	ID6		(Note 2)
:			
FFFBh	ID7		(Note 2)
:			
FFFFh	Option Function Select Register	OFS	(Note 1)

Notes:
1. The option function select area is allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the option function select area. If the block including the option function select area is erased, the option function select area is set to FFh.
   When blank products are shipped, the option function select area is set to FFh. It is set to the written value after written by the user.
   When factory-programming products are shipped, the value of the option function select area is the value programmed by the user.
2. The ID code areas are allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
   Do not write additions to the ID code areas. If the block including the ID code areas is erased, the ID code areas are set to FFh.
   When blank products are shipped, the ID code areas are set to FFh. They are set to the written value after written by the user.
   When factory-programming products are shipped, the value of the ID code areas is the value programmed by the user.

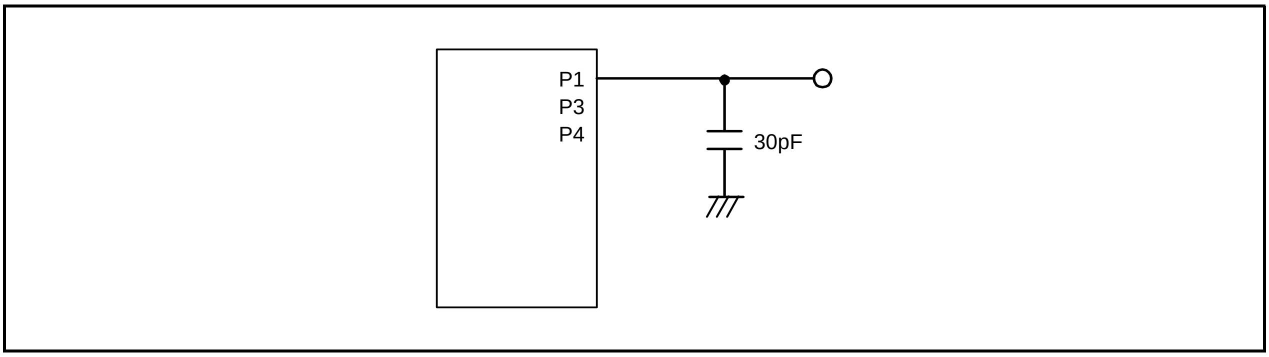


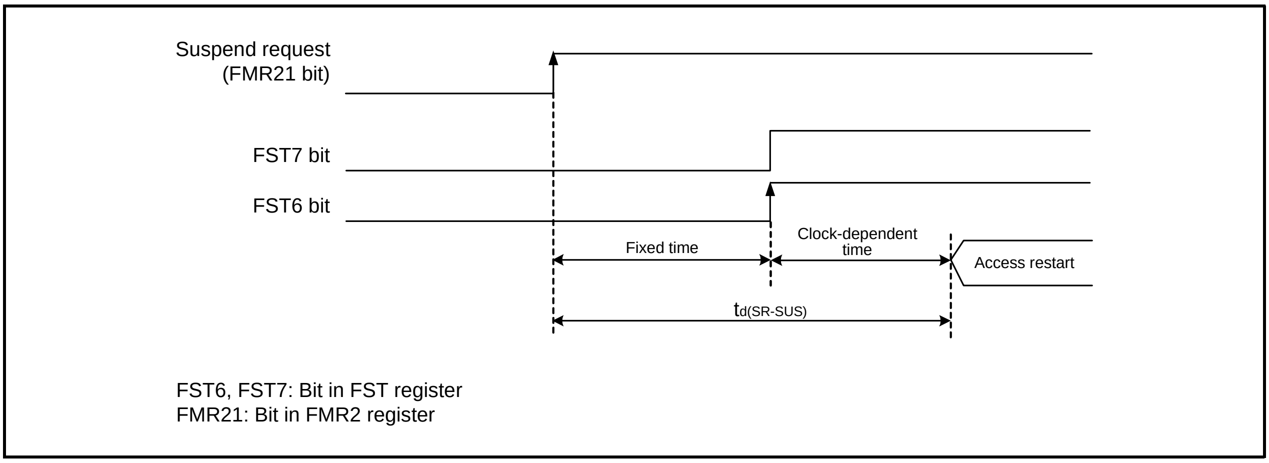
Figure 5.1 **Ports P1, P3, P4 Timing Measurement Circuit**

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		10,000 (3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	160	1,500	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	300	1,500	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	1	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5 + CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 (7)	–	85	°C
–	Data hold time (8)	Ambient temperature = 55 °C	20	–	–	year

Notes:

1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40°C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.



FST6, FST7: Bit in FST register
FMR21: Bit in FMR2 register

Figure 5.2 Time delay until Suspend

Table 5.10 Voltage Detection 2 Circuit Electrical Characteristics

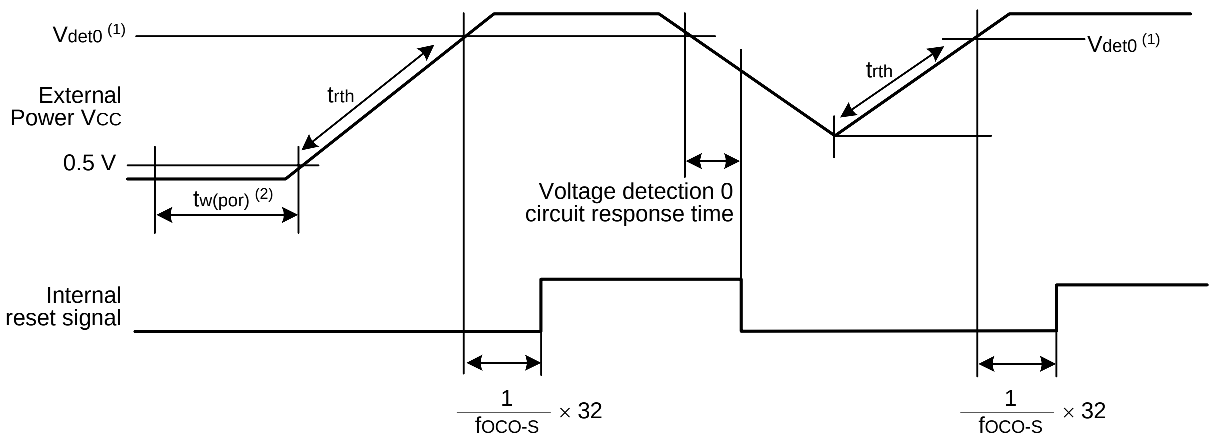
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0 (2)	At the falling of V_{CC}	3.70	4.00	4.30	V
	Voltage detection level Vdet2_EXT (2)	At the falling of LVCMP2	1.20	1.34	1.48	V
–	Hysteresis width at the rising of Vcc in voltage detection 2 circuit		–	0.10	–	V
–	Voltage detection 2 circuit response time (3)	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	20	150	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. The voltage detection level varies with detection targets. Select the level with the VCA24 bit in the VCA2 register.
3. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
4. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.11 Power-on Reset Circuit (2)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{rth}	External power V_{CC} rise gradient	(1)	0	–	50,000	mV/ms

Notes:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



Notes:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of User's Manual: Hardware for details.
2. $t_{w(por)}$ indicates the duration the external power V_{CC} must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain $t_{w(por)}$ for 1 ms or more.

Figure 5.3 Power-on Reset Circuit Electrical Characteristics

Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V $-20°C \le T_{opr} \le 85°C$	39.4	40	40.6	MHz
		V_{CC} = 1.8 V to 5.5 V $-40°C \le T_{opr} \le 85°C$	39.4	40	40.6	MHz
		V_{CC} = 1.8 V to 5.5 V T_{opr} = 25°C	39.6	40	40.4	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V $-20°C \le T_{opr} \le 85°C$	36.311	36.864	37.417	MHz
		V_{CC} = 1.8 V to 5.5 V $-40°C \le T_{opr} \le 85°C$	36.311	36.864	37.417	MHz
		V_{CC} = 1.8 V to 5.5 V T_{opr} = 25°C	36.495	36.864	37.233	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V $-20°C \le T_{opr} \le 85°C$	31.52	32	32.48	MHz
		V_{CC} = 1.8 V to 5.5 V $-40°C \le T_{opr} \le 85°C$	31.52	32	32.48	MHz
		V_{CC} = 1.8 V to 5.5 V T_{opr} = 25°C	31.68	32	32.32	MHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	100	450	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	500	–	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

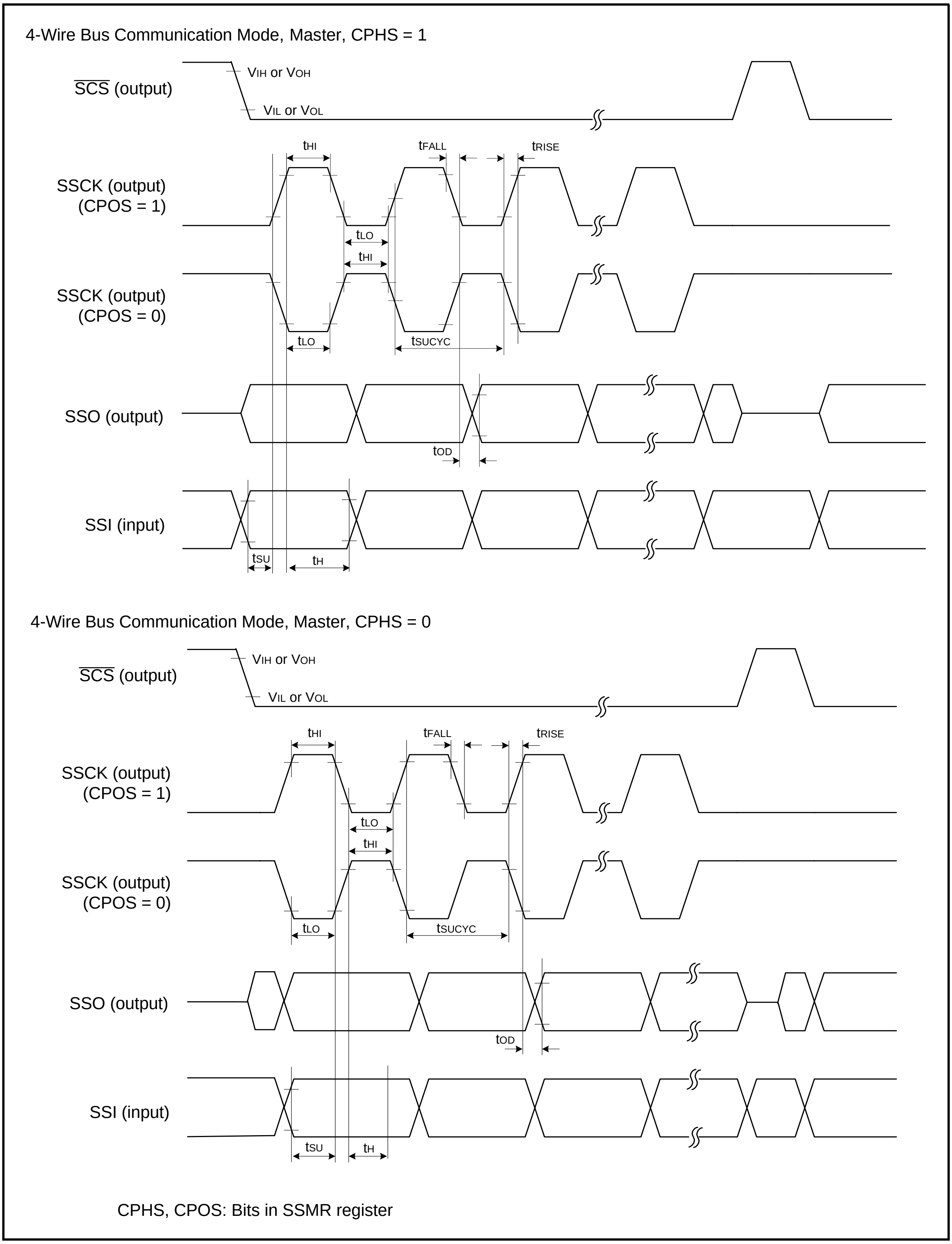
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
f_{OCO-S}	Low-speed on-chip oscillator frequency		60	125	250	kHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	30	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	2	–	µA
$f_{OCO-WDT}$	Low-speed on-chip oscillator frequency for the watchdog timer		60	125	250	kHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	30	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	2	–	µA

Note:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.14 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		–	–	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.



CPHS, CPOS: Bits in SSMR register

Figure 5.4 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)

Table 5.18 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.2	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	85	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	47	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Table 5.23 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 µA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$, $\overline{\text{KI0}}$, $\overline{\text{KI1}}$, $\overline{\text{KI2}}$, $\overline{\text{KI3}}$, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, $\overline{\text{TRCTRG}}$, TRCCLK, $\overline{\text{ADTRG}}$, RXD0, RXD2, CLK0, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 3.0 V		0.1	0.4	–	V
		$\overline{\text{RESET}}$	V_{CC} = 3.0 V		0.1	0.5	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3.0 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3.0 V		–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:

1. 2.7 V ≤ V_{CC} < 4.2 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.29 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output "H" voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	–	V_{CC}	V
V_{OL}	Output "L" voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$, KI0, KI1, KI2, KI3, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, $\overline{\text{TRCTRG}}$, TRCCLK, $\overline{\text{ADTRG}}$, RXD0, RXD2, CLK0, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 2.2 V		0.05	0.2	–	V
		$\overline{\text{RESET}}$	V_{CC} = 2.2 V		0.05	0.20	–	V
I_{IH}	Input "H" current		VI = 2.2 V, V_{CC} = 2.2 V		–	–	4.0	μA
I_{IL}	Input "L" current		VI = 0 V, V_{CC} = 2.2 V		–	–	–4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:

1. 1.8 V ≤ V_{CC} < 2.7 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

Table 5.30 Electrical Characteristics (6) [$1.8\ V \leq V_{CC} < 2.7\ V$]
(T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 1.8 to 2.7 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	2.2	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	0.8	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on f_{OCO-F} = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	2.5	10	mA
			XIN clock off High-speed on-chip oscillator on f_{OCO-F} = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.7	–	mA
			XIN clock off High-speed on-chip oscillator on f_{OCO-F} = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	80	350	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, T_{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5	µA
			XIN clock off, T_{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Table 5.33 Serial Interface

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	When external clock is selected	800	–	ns
$t_{W(CKH)}$	CLKi input “H” width		400	–	ns
$t_{W(CKL)}$	CLKi input “L” width		400	–	ns
$t_{d(C-Q)}$	TXDi output delay time		–	200	ns
$t_{h(C-Q)}$	TXDi hold time		0	–	ns
$t_{su(D-C)}$	RXDi input setup time		150	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns
$t_{d(C-Q)}$	TXDi output delay time	When internal clock is selected	–	200	ns
$t_{su(D-C)}$	RXDi input setup time		150	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns

i = 0, 2

Note:

1. Vcc = 2.2 V and Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.

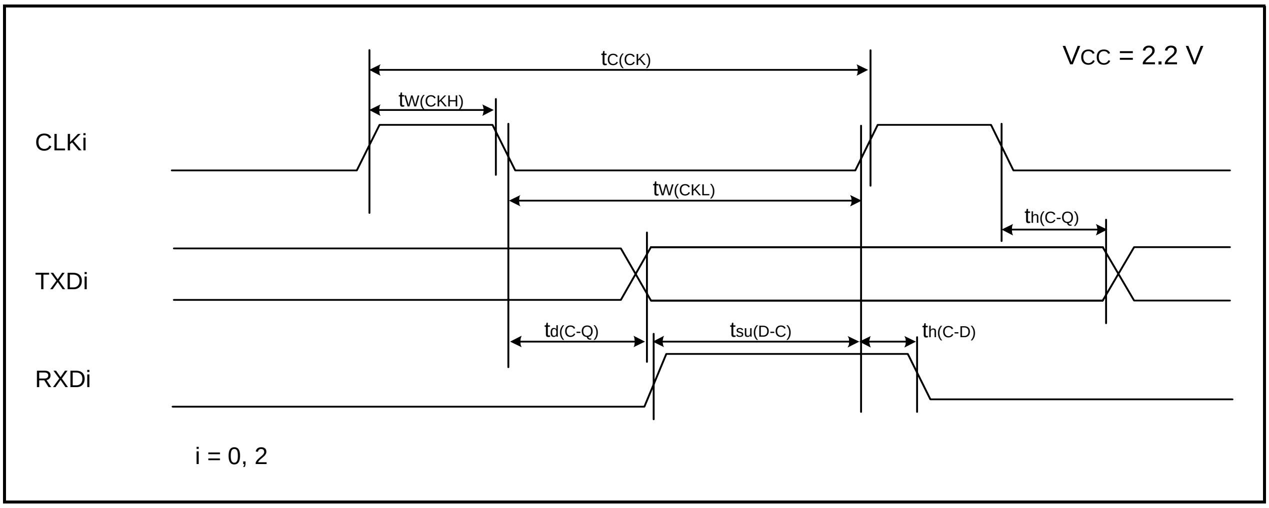


Figure 5.18 Serial Interface Timing Diagram when Vcc = 2.2 V

Table 5.34 External Interrupt $\overline{\text{INTi}}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{\text{KIi}}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{\text{INTi}}$ input “H” width, $\overline{\text{KIi}}$ input “H” width	1000 (1)	–	ns
$t_{W(INL)}$	$\overline{\text{INTi}}$ input “L” width, $\overline{\text{KIi}}$ input “L” width	1000 (2)	–	ns

Notes:

1. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

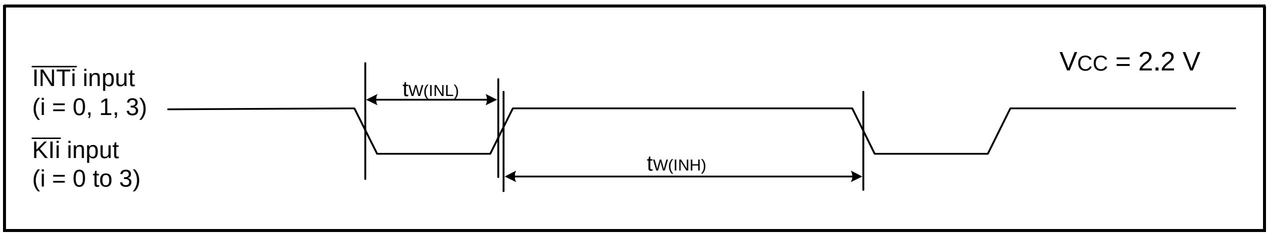
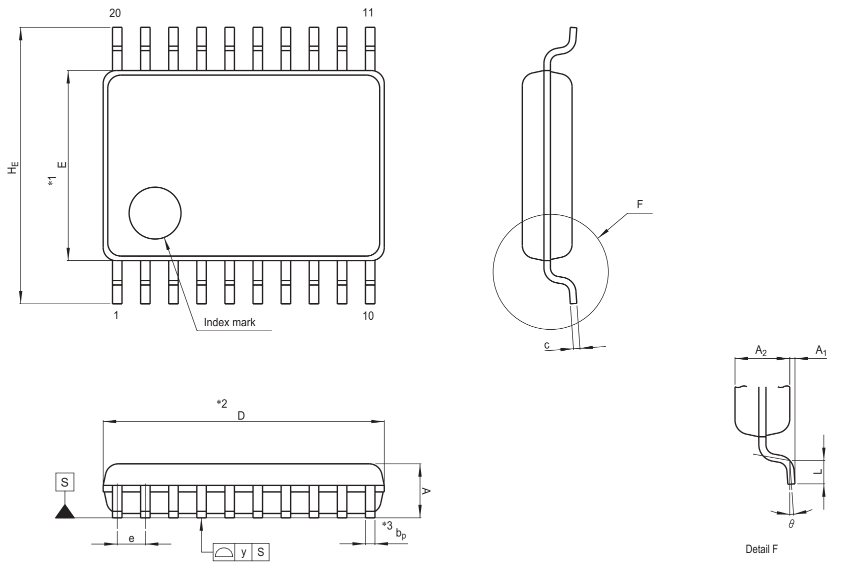


Figure 5.19 Input Timing for External Interrupt $\overline{\text{INTi}}$ and Key Input Interrupt $\overline{\text{KIi}}$ when Vcc = 2.2 V

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Electronics website.

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	20P2F-A	0.1g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.4	6.5	6.6
E	4.3	4.4	4.5
A_2	—	1.15	—
A	—	—	1.45
A_1	0	0.1	0.2
b_p	0.17	0.22	0.32
c	0.13	0.15	0.2
θ	0°	—	10°
H_E	6.2	6.4	6.6
e	0.53	0.65	0.77
y	—	—	0.10
L	0.3	0.5	0.7

General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

   Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

   — The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

2. Processing at Power-on

   The state of the product is undefined at the moment when power is supplied.

   — The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.

   In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

   In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

3. Prohibition of Access to Reserved Addresses

   Access to reserved addresses is prohibited.

   — The reserved addresses are provided for the possible future expansion of functions. Do not access these addresses; the correct operation of LSI is not guaranteed if they are accessed.

4. Clock Signals

   After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

   — When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.

5. Differences between Products

   Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

   — The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.